

Abstract of the Disclosure

An internal voltage generating circuit in a semiconductor memory device includes a comparing unit for comparing a voltage level of an internal voltage with that of a reference voltage, a pull-up driving unit for performing a pull-up operation for an output terminal in response to an output signal of the comparing unit, and a discharging unit for discharging the output terminal in a period of which the voltage level of the internal voltage is higher than a predetermined target voltage level.